

# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 6)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-4.2 -3.4	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-10	Α

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		$P_{D}$	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	100	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	74	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

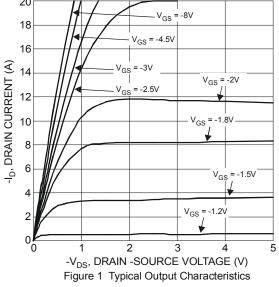
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

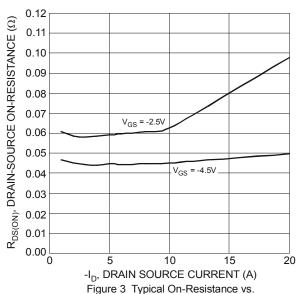
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>		_	-1.0	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	45	65	mΩ	$V_{GS} = -4.5V$ , $I_D = -4.2A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		57	100		$V_{GS}$ = -2.5V, $I_{D}$ = -3.4A	
	, ,		80	200		$V_{GS} = -1.8V, I_D = -2A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	9	_	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4A	
DYNAMIC CHARACTERISTICS (Note 8)			•	•			
Input Capacitance	C <sub>iss</sub>		845	_	pF		
Output Capacitance	Coss		72	_	pF	$V_{DS}$ = -15V, $V_{GS}$ = 0V -f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	63	_	pF	1 - 1.000112	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	Qg		10.4	_	nC	451414	
Gate-Source Charge	$Q_{gs}$	_	1.5	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -4V$ , $-I_{D} = -3.5A$	
Gate-Drain Charge	$Q_{gd}$	_	1.9	_	nC	JID = -3.3M	
Turn-On Delay Time	t <sub>D(on)</sub>	_	6.5	_	ns		
Turn-On Rise Time	t <sub>r</sub>		13.4	_	ns	V <sub>DS</sub> = -4V, V <sub>GS</sub> = -4.5V,	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	51.5	_	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>f</sub>		21.8	_	ns	7	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

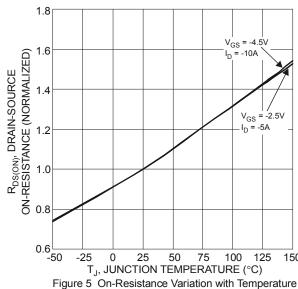
<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

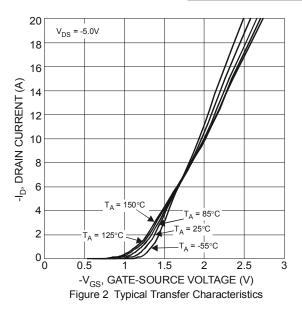


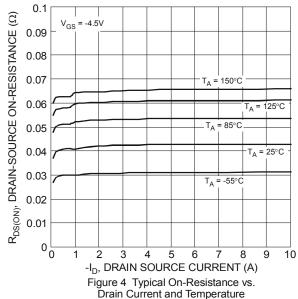


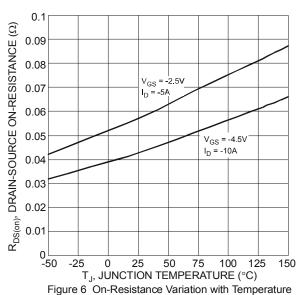


Drain Current and Gate Voltage









DMP2033UVT



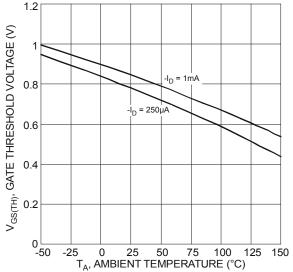
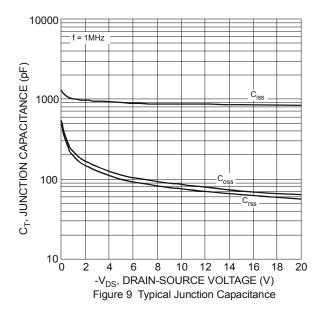
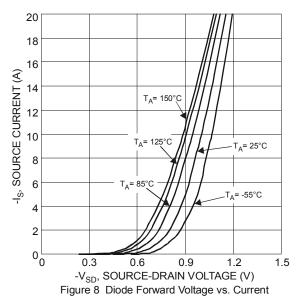
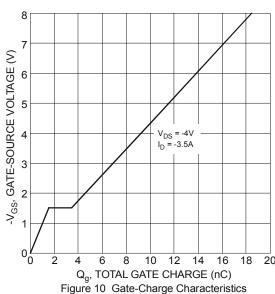


Figure 7 Gate Threshold Variation vs. Ambient Temperature

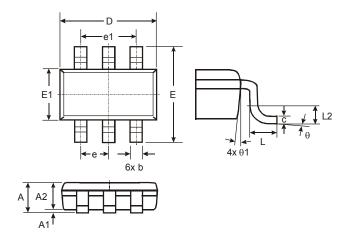






### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TSOT26					
Dim	Min	Max	Тур		
Α	_	1.00	-		
<b>A</b> 1	0.01	0.10	-		
A2	0.84	0.90	-		
D	_	_	2.90		
Е	_	_	2.80		
E1	_	_	1.60		
b	0.30	0.45	-		
С	0.12	0.20	-		
е	_	-	0.95		
e1	_	_	1.90		
L	0.30	0.50			
L2	_	_	0.25		
θ	0°	8°	4°		
θ1	4°	12°	_		
All Dimensions in mm					

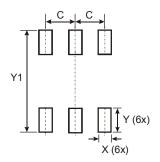
March 2014

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#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.950
Х	0.700
Υ	1.000
Y1	3.199

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